MSKSEMI 美森科













ESD

TVS

SS

MOV

GDT

PIFD

MMBTA92-MS

Product specification





TRANSISTOR (PNP)

FEATURES

High voltage transistor

Reference News

PACKAGE OUTLINE		MARKING	
1 2	1. BASE 2. EMITTER 3.COLLECTOR	2 D	
SOT-23			

MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

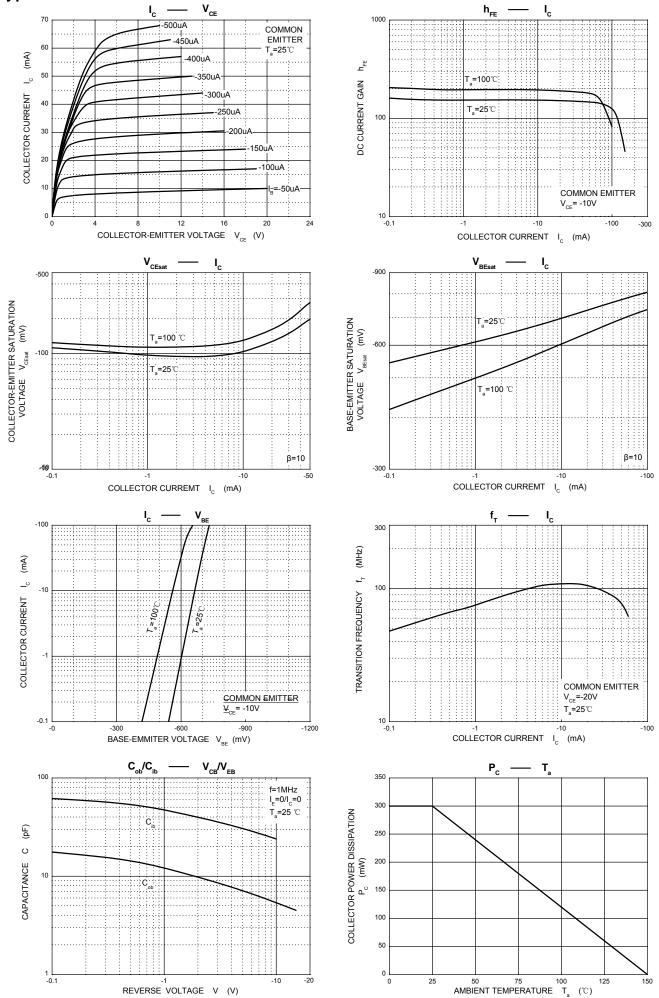
Symbol	Parameter	Value	Unit
V _{СВО}	Collector-Base Voltage	-300	V
V _{CEO}	Collector-Emitter Voltage	-300	V
V _{EBO}	Emitter-Base Voltage	-5	V
lc	Collector Current -Continuous	-200	mA
Ісм	Collector Current -Pulsed	-500	mA
Pc	Collector Power Dissipation	300	mW
Tj	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C
R _{OJA}	Thermal Resistance from Junction to Ambient	417	°C/W

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -100μΑ, I _E =0	-300		V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -1mA, I _B =0	-300		V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -100μΑ, I _C =0	-5		V
Collector cut-off current	I _{CBO}	V _{CB} =-200V, I _E =0		-0.25	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -5V, I _C =0		-0.1	μA
	h _{FE(1)}	V _{CE} = -10V, I _C = -1mA	60		
DC current gain	h _{FE(2)}	V _{CE} = -10V, I _C =-10mA	100	200	
	h _{FE(3)}	V _{CE} = -10V, I _C =-30mA	60		
Collector-emitter saturation voltage	V _{CE} (sat)	lc=-20mA, I _B = -2mA		-0.2	V
Base-emitter saturation voltage	V _{BE} (sat)	I _C = -20mA, I _B = -2mA		-0.9	V
Transition frequency	f⊤	V _{CE} =-20V, I _C = -10mA f=30MHz	50		MHz

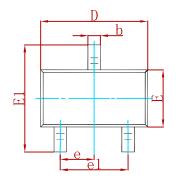


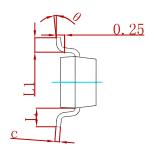
Typical Characteristics

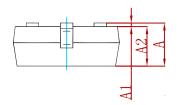




PACKAGE MECHANICAL DATA

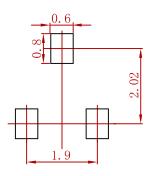






Cumbal	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
Е	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

Suggested Pad Layout



Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
MMBTA92-MS	SOT-23	3000



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